

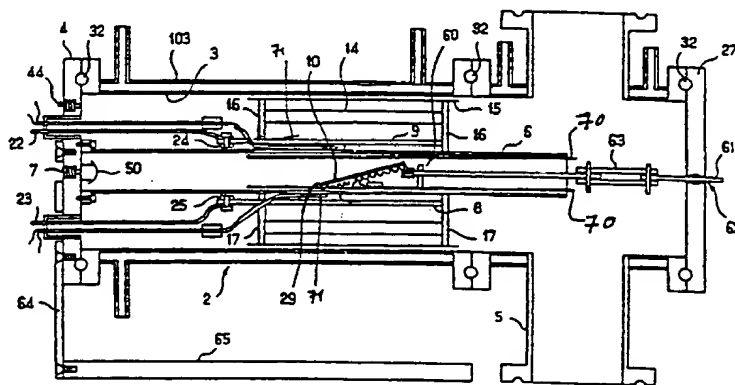
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(54) Title: REACTOR AND METHOD FOR CHEMICAL VAPOUR DEPOSITION

(54) Titre: REACTEUR ET PROCÉDE POUR DÉPÔT CHIMIQUE EN PHASE VAPEUR



(57) Abstract

The invention concerns a method for chemical vapour deposition of coats of a material on a substrate (10) extending globally in a plane, comprising: a step which consists in arranging the substrate (10) in a conduit (6) made of a refractory material and swept by the gas components required for deposition, said conduit (6) being interposed between the substrate (10) and first (8) and second (9) heating means, located on either side of the substrate (10) plane, characterised in that it further comprises a step which consists in heating the substrate (10) by the thermal radiation from the conduit (6) which is itself heated by the first (8) and second (9) heating means.

(57) Abrégé

L'invention concerne un procédé de dépôt en phase vapeur, de couches d'un matériau sur un substrat (10) s'étendant globalement dans un plan, comprenant une étape consistant à disposer le substrat (10) dans un conduit (6) constitué d'un matériau réfractaire et balayé par les composés gazeux nécessaires au dépôt, ce conduit (6) étant interposé entre le substrat (10) et des premiers (8) et deuxièmes (9) moyens de chauffage, situés de part et d'autre du plan du substrat (10), caractérisé par le fait qu'il comprend en outre, une étape consistant à chauffer le substrat (10) grâce au rayonnement de la chaleur du conduit (6), lui-même chauffé par les premiers (8) et deuxièmes (9) moyens de chauffage.

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